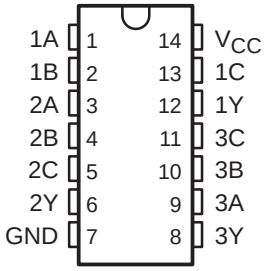
SCES106D – JULY 1997 – REVISED OCTOBER 1998

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (D), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages**

D, DGV, OR PW PACKAGE
(TOP VIEW)



description

This triple 3-input positive-NAND gate is designed for 1.65-V to 3.6-V V_{CC} operation.

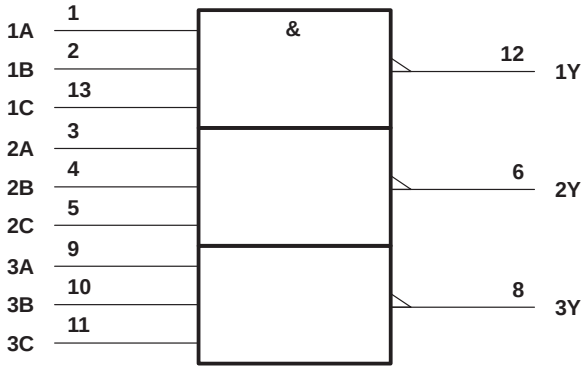
The SN74ALVC10 performs the Boolean function $Y = \overline{A \bullet B \bullet C}$ or $Y = \overline{A} + \overline{B} + \overline{C}$ in positive logic.

The SN74ALVC10 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

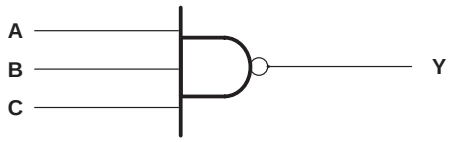
INPUTS			OUTPUT
A	B	C	Y
H	H	H	L
L	X	X	H
X	L	X	H
X	X	L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each gate (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0) . . . . . –50 mA
Continuous output current, I_O . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): D package . . . . . 127°C/W
DGV package . . . . . 182°C/W
PW package . . . . . 170°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		1.65	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 1.65 V to 1.95 V		0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 1.65 V		–4	mA
		V_{CC} = 2.3 V		–12	
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 1.65 V		4	mA
		V_{CC} = 2.3 V		12	
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	5	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		1.65 V to 3.6 V	V_{CC}–0.2			V
	I_{OH} = –4 mA		1.65 V	1.2			
	I_{OH} = –6 mA		2.3 V	2			
	I_{OH} = –12 mA		2.3 V	1.7			
			2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2			
V_{OL}	I_{OL} = 100 µA		1.65 V to 3.6 V			0.2	V
	I_{OL} = 4 mA		1.65 V			0.45	
	I_{OL} = 6 mA		2.3 V			0.4	
	I_{OL} = 12 mA		2.3 V			0.7	
			2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	$V_I = V_{CC}$ or GND		3.6 V			±5	µA
I_{CC}	$V_I = V_{CC}$ or GND,	I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	$V_I = V_{CC}$ or GND		3.3 V		4		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

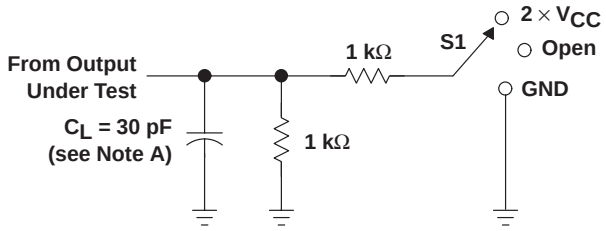
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A, B, or C	Y	1.1	4.8	1	3		3.3	1	3	ns

operating characteristics, T_A = 25°C

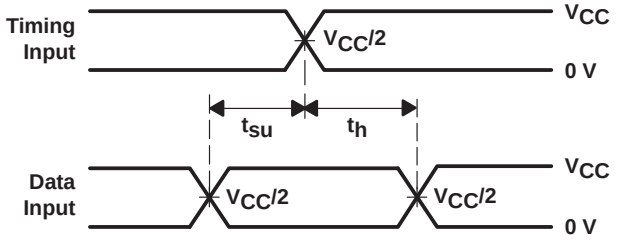
PARAMETER		TEST CONDITIONS		V_{CC} = 1.8 V	V_{CC} = 2.5 V	V_{CC} = 3.3 V	UNIT
				TYP	TYP	TYP	
C_{pd}	Power dissipation capacitance per gate	C_L = 0,	f = 10 MHz	23	24	26	pF

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 1.8 V ± 0.15 V

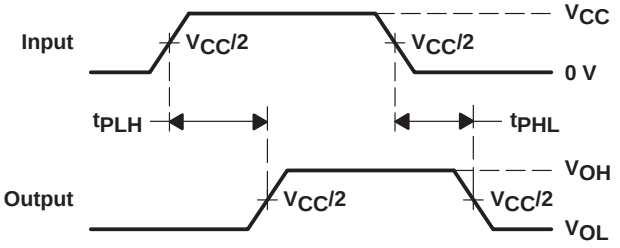


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	Open

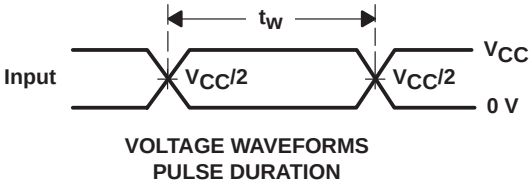
LOAD CIRCUIT



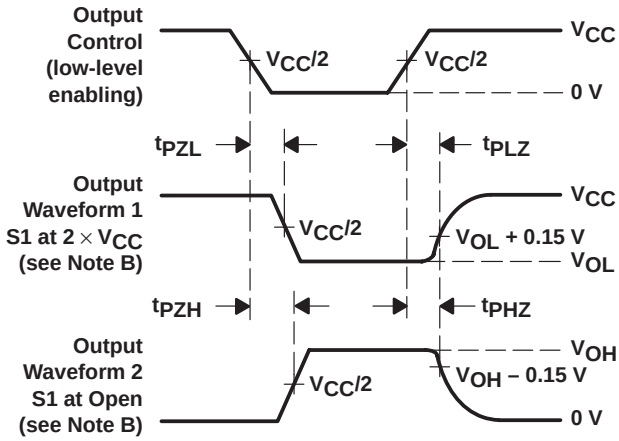
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

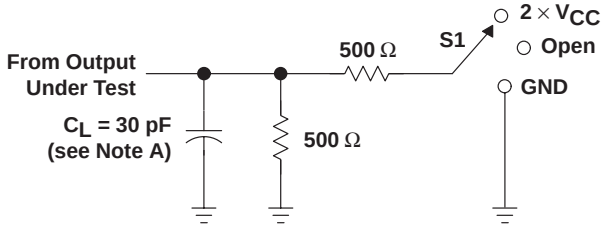


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR≤10 MHz, Z_O = 50 Ω, t_r≤2 ns, t_f≤2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

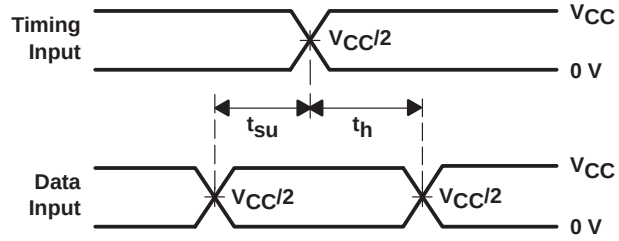
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

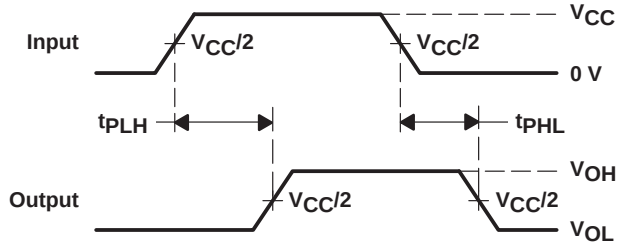


TEST	S1
t_{pd} t_{PLZ}/t_{PZL} t_{PHZ}/t_{PZH}	Open 2 × V_{CC} GND

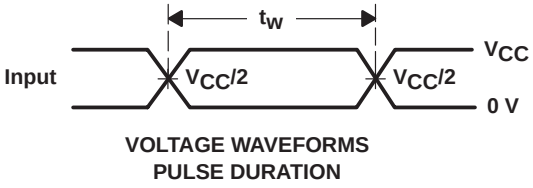
LOAD CIRCUIT



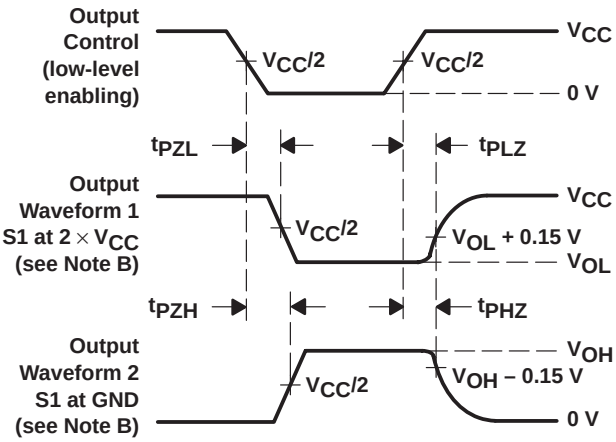
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
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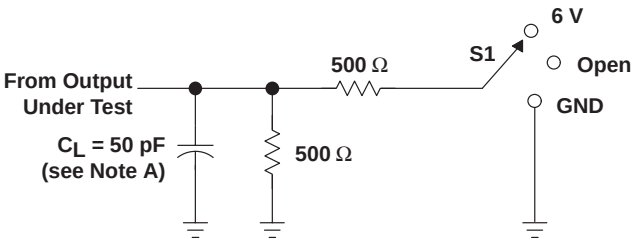
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

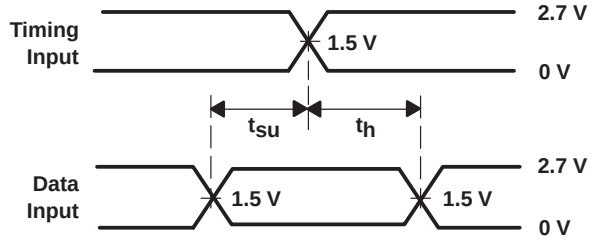
Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

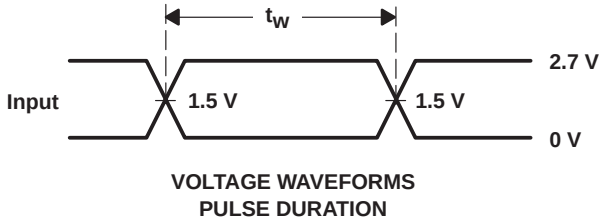


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

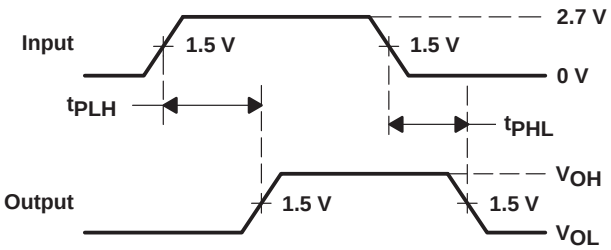
LOAD CIRCUIT



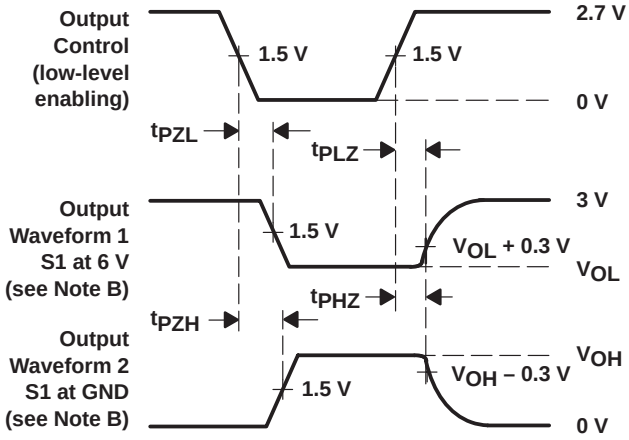
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



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F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 3. Load Circuit and Voltage Waveforms

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